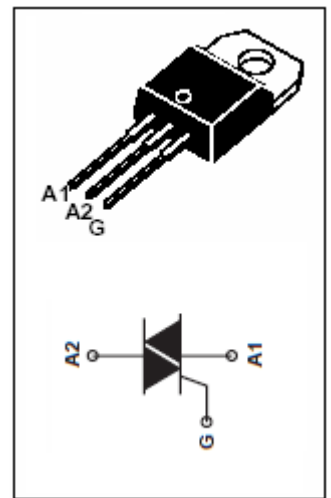


FEATURES

- With TO-220AB insulated package
- Suitable for application such as phase control and static switching on inductive or resistive load.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	600	V
V_{RRM}	Repetitive peak reverse voltage	600	V
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_j=70^{\circ}\text{C}$	20	A
I_{TSM}	Non-repetitive peak on-state current $t_p=10\text{ms}$	200	A
T_j	Operating junction temperature	110	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-45~150	$^{\circ}\text{C}$
$R_{th(j-c)}$	Thermal resistance, junction to case	2.8	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	Thermal resistance, junction to ambient	60	$^{\circ}\text{C/W}$



ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise specified)

SYMBOL	PARAMETER		CONDITIONS	MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current		$V_R=V_{RRM}$, $V_R=V_{RRM}$, $T_j=110^{\circ}\text{C}$		0.01 2.0	mA
I_{DRM}	Repetitive peak off-state current		$V_D=V_{DRM}$, $V_D=V_{DRM}$, $T_j=110^{\circ}\text{C}$		0.01 2.0	mA
I_{GT}	Gate trigger current	I - II -III	$V_D=12\text{V}$; $R_L=33\Omega$	1	35	mA
I_H	Holding current		$I_{GT}=0.5\text{A}$, Gate Open		50	mA
V_{GT}	Gate trigger voltage	I - II -III	$V_D=12\text{V}$; $R_L=33\Omega$		1.5	V
V_{TM}	On-state voltage		$I_T=28\text{A}$; $t_p=380\mu\text{s}$		1.7	V